

ABSTRACT

5 Provided is a hafnium silicide target for forming a gate oxide film composed of $\text{HfSi}_{0.82-0.98}$, wherein the oxygen content is 500 to 10000ppm. Manufactured is a hafnium silicide target for forming a gate oxide film, wherein powder of the composition composed of $\text{HfSi}_{0.82-0.98}$ is synthesized, pulverized to be 100 mesh or less, and thereafter subject to hot pressing or hot isostatic pressing (HIP) at 1700°C to 2120°C and 150 to 2000kgf/cm^2 .
10 Thereby obtained is a hafnium silicide target, and the manufacturing method thereof, suitable for forming a HfSiO film and HfSiON film that may be used as a high dielectric gate insulation film, superior in embrittlement resistance, having a low generation of particles, and which is not likely to cause ignition of sintering powder or explosion of powder dust during the manufacturing process thereof.



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